TOSHIBA

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

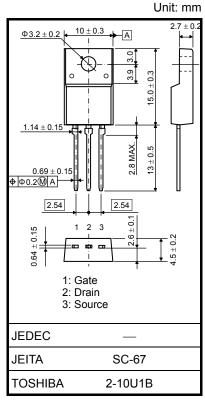
# **TK11A50D**

#### Switching Regulator Applications

- Low drain-source ON-resistance: R<sub>DS (ON)</sub> = 0.45 Ω (typ.)
- High forward transfer admittance: |Y<sub>fs</sub>| = 5.5 S (typ.)
- Low leakage current:  $I_{DSS}$  = 10  $\mu$ A (max) (V<sub>DS</sub> = 500 V)
- Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	500	V
Gate-source voltage		V <sub>GSS</sub>	±30	V
Drain current	DC (Note 1)	ID	11	
	Pulse (t = 1 ms) (Note 1)	I <sub>DP</sub>	44	A
Drain power dissipation (Tc = 25°C)		PD	45	W
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	264	mJ
Avalanche current		I <sub>AR</sub>	11	А
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	4.5	mJ
Channel temperature	1	T <sub>ch</sub>	150	°C
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C

#### Absolute Maximum Ratings (Ta = 25°C)



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

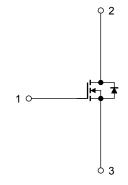
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}C(\text{initial}), \text{ L} = 3.7 \text{ mH}, \text{ R}_{G} = 25 \Omega, \text{ I}_{AR} = 11 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



Start of commercial production 2009-05

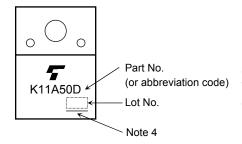
**Electrical Characteristics (Ta = 25°C)** 

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS}=\pm 30~V,~V_{DS}=0~V$	_		±1	μA
Drain cut-off curr	ent	I <sub>DSS</sub>	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_		10	μA
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	500			V
Gate threshold ve	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.0		4.0	V
Drain-source ON	-resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 5.5 \text{ A}$	—	0.45	0.6	Ω
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 5.5 \text{ A}$	1.4	5.5		S
Input capacitance		C <sub>iss</sub>		_	1200		
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		6		pF
Output capacitance		C <sub>oss</sub>			120		
Switching time	Rise time	tr	$\begin{array}{c} 10 \text{ V} \\ \text{V}_{GS} \\ 0 \text{ V} \\ 50 \Omega \\ \end{array} \begin{array}{c} \text{I}_{D} = 5.5 \text{ A} \\ \text{V}_{OUT} \\ \text{V}_{GS} \\ \text{V}_{DD} \approx 200 \text{ V} \\ \text{V}_{DD} \approx 200 \text{ V} \\ \end{array}$		25	_	
	Turn-on time	t <sub>on</sub>		_	60	_	- ns
	Fall time	t <sub>f</sub>			12		
	Turn-off time	t <sub>off</sub>		_	100		
Total gate charge		Qg			24		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 11 \text{ A}$		16		nC
Gate-drain charge		Q <sub>gd</sub>	]		8	_	

#### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	11	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	44	А
Forward voltage (diode)	V <sub>DSF</sub>	$I_{DR} = 11 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 11 A, V <sub>GS</sub> = 0 V,	_	1300	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dl <sub>DR</sub> /dt = 100 A/μs		12	_	μC

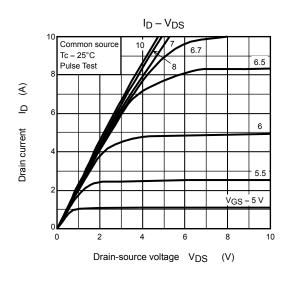
#### Marking

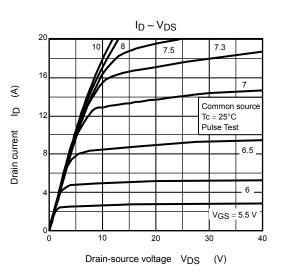


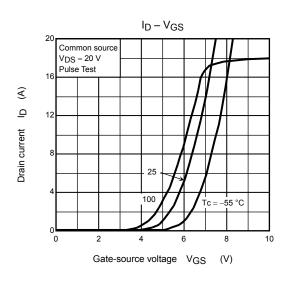
Note 4 : A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

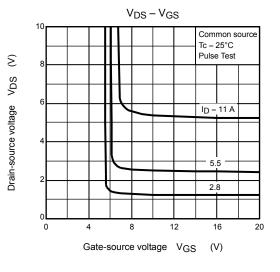
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

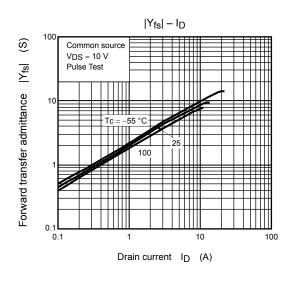
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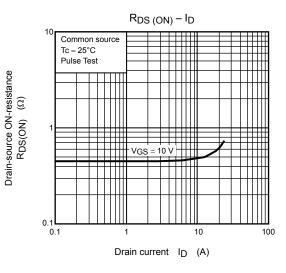




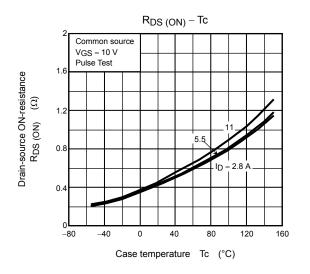


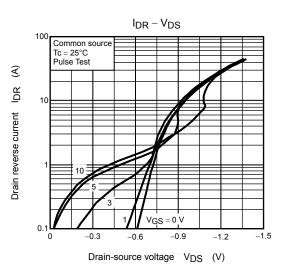


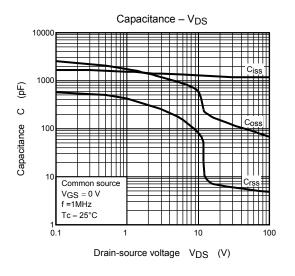




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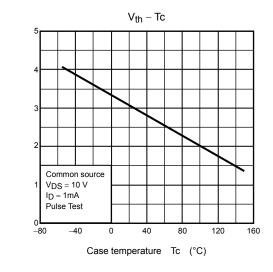
P<sub>D</sub> – Tc

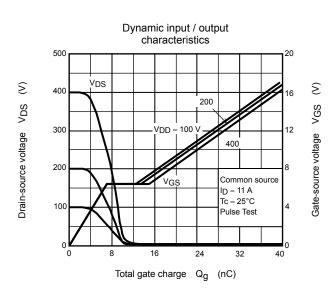
80

Case temperature Tc (°C)

120

160

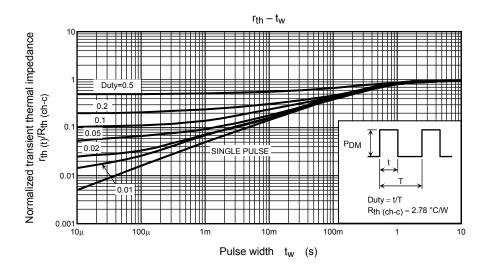




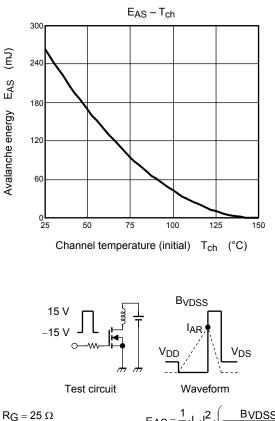
Drain power dissipation DD (M)

Gate threshold voltage Vth

S



SAFE OPERATING AREA 100 ID max (pulse) \* ID max (continuous) 100 us \* 10 E Drain current I<sub>D</sub> DC operation Tc = 25°C 0.1 0.01 Single pulse Tc=25°C Curves must be derated linearly with increase in temperature. V<sub>DSS</sub> max 0.001 10 100 1000 1 Drain-source voltage  $V_{DS}$  (V)



$R_{G} = 25 \Omega$	$E_{AS} = \frac{1}{2} \cdot L \cdot l^2 \cdot L$	$\left(\frac{BVDSS}{BVDSS}-VDD}\right)$	
V <sub>DD</sub> = 90 V, L = 3.7 mH	2	(BVDSS-VDD)	

## <u>TOSHIBA</u>

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